

The following Listing of Claims will replace all prior versions, and listings, of claims in the application.

LISTING OF CLAIMS:

1. (Currently Amended) A semiconductor device, comprising:

a unitary and non-layered semiconductor substrate comprising a thin portion that is thinner than adjacent portions of the semiconductor substrate, and a recessed portion formed below the thin portion, the thin portion being configured and arranged to bridge both sides of the recessed portion and strengthen the semiconductor substrate with respect to forces applied from both sides of the semiconductor substrate;

wherein the etching rate of the thin portion is slower than that of the surrounding portions of the semiconductor substrate;

at least one through hole is formed in the thin portion that extends from the recessed portion, and entirely through the thin portion to the upper surface of the semiconductor substrate; and

a dopant is infused in at least a portion of the thin portion ~~that is immediately adjacent to the at least one through hole.~~

4. (Original) The semiconductor device set forth in claim 1, wherein the thin portion is formed by means of a selective oxide film.

13. (Previously Presented) The semiconductor device set forth in claim 1, wherein

the dopant is infused in the entire thin portion.